

## P-Channel Enhancement Mode Vertical DMOS FETs

### **Features**

- Low threshold
- High input impedance
- Low input capacitance
- Fast switching speeds
- Low on-resistance
- ▶ Free from secondary breakdown
- Low input and output leakage

### **Applications**

- Logic level interfaces
- Solid state relays
- Linear amplifiers
- Power management
- Analog switches
- Telecom switches

### **General Description**

This low threshold enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

### **Ordering Information**

Device	Package Option	$BV_{DSS}/BV_{DGS}$	$R_{DS(ON)}$	$V_{GS(th)}$	I <sub>D(ON)</sub>
	TO-243AA (SOT-89)	(V)	(max) (Ω)	(max) (V)	(min) (mA)
TP2435	TP2435N8-G	-350	15	-2.4	-800

-G indicates package is RoHS compliant ('Green')





## **Absolute Maximum Ratings**

Parameter	Value
Drain-to-source voltage	BV <sub>DSS</sub>
Drain-to-gate voltage	$BV_{DGS}$
Gate-to-source voltage	±20V
Operating and storage temperature	-55°C to +150°C
Soldering temperature*	300°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

## **Pin Configuration**



TO-243AA (SOT-89) (N8)

## **Product Marking**

TP4SW

W = Code for week sealed
\_\_\_\_\_ = "Green" Packaging

Package may or may not include the following marks: Si or

TO-243AA (SOT-89) (N8)

<sup>\*</sup> Distance of 1.6 mm from case for 10 seconds.

## **Thermal Characteristics**

Package	l <sub>D</sub> (continuous) <sup>†</sup> (mA)	I <sub>D</sub> (pulsed) (A)	Power Dissipation @ T <sub>A</sub> = 25°C (W)	θ <sub>jc</sub> (°C/W)	θ <sub>ja</sub> (°C/W)	†   <sub>DR</sub> (mA)	I <sub>DRM</sub> (A)
TO-243AA (SOT-89)	-231	-1.1	1.6	15	78 <sup>‡</sup>	-231	-1.1

<sup>†</sup>  $I_D$  (continuous) is limited by max rated  $T_i$ .

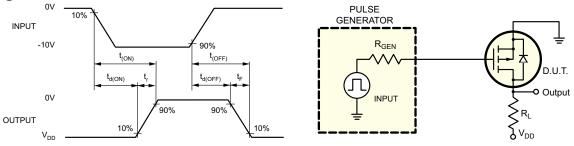
## **Electrical Characteristics** (T<sub>A</sub> = 25°C unless otherwise specified)

Sym	Parameter	Min	Тур	Max	Units	Conditions	
BV <sub>DSS</sub>	Drain-to-source breakdown voltage	-350	-	-	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
V <sub>GS(th)</sub>	Gate threshold voltage	-1.0	-	-2.4	V	$V_{GS} = V_{DS}$ , $I_D = -1.0$ mA	
$\Delta V_{GS(th)}$	Change in $V_{\text{GS(th)}}$ with temperature	-	-	4.5	mV/°C	$V_{GS} = V_{DS}$ , $I_{D} = -1.0$ mA	
I <sub>GSS</sub>	Gate body leakage	-	-	-100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
			-	-10	μA	$V_{GS} = 0V, V_{DS} = Max Rating$	
I <sub>DSS</sub>	Zero gate voltage drain current	-	-	-1.0	mA	$V_{DS} = 0.8$ Max Rating, $V_{GS} = 0V$ , $T_{A} = 125$ °C	
ı	On-state drain current	-0.3	-	-	Α	$V_{GS} = -4.5V, V_{DS} = -25V$	
I <sub>D(ON)</sub>	On-State drain current	-0.8	-	-	_ A	$V_{GS} = -10V, V_{DS} = -25V$	
	Static drain-to-source on-state resistance	-	-	15		$V_{GS} = -3.0V, I_{D} = -20mA$	
R <sub>DS(ON)</sub>		_	-	15	Ω	$V_{GS} = -4.5V, I_{D} = -150mA$	
, ,		-	-	15		V <sub>GS</sub> = -10V, I <sub>D</sub> = -500mA	
$\Delta R_{DS(ON)}$	Change in R <sub>DS(ON)</sub> with temperature	-	-	1.7	%/°C	V <sub>GS</sub> = -10V, I <sub>D</sub> = -150mA	
G <sub>FS</sub>	Forward transconductance	125	-	-	mmho	$V_{DS} = -25V, I_{D} = -350mA$	
C <sub>ISS</sub>	Input capacitance	-	-	200		V <sub>GS</sub> = 0V,	
C <sub>oss</sub>	Common source output capacitance	_	-	70	pF	$V_{DS} = -25V,$	
C <sub>RSS</sub>	Reverse transfer capacitance	-	-	25		f = 1.0 MHz	
t <sub>d(ON)</sub>	Turn-on delay time	-	-	15			
t <sub>r</sub>	Rise time	-	-	20	200	V <sub>DD</sub> = -25V,	
t <sub>d(OFF)</sub>	Turn-off delay time		-	25	ns	$I_D = -250 \text{mA},$ $R_{GEN} = 25\Omega$	
t <sub>f</sub>	Fall time	-	-	50		GEN	
V <sub>SD</sub>	Diode forward voltage drop	-	-	-1.5	V	$V_{GS} = 0V, I_{SD} = -750 \text{mA}$	
t <sub>rr</sub>	Reverse recovery time	-	300	-	ns	$V_{GS} = 0V, I_{SD} = -750 \text{mA}$	

#### Notes:

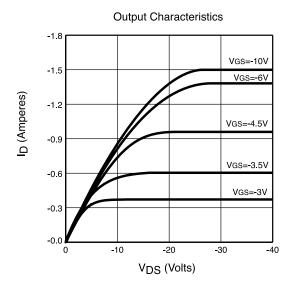
- 1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)
- 2. All A.C. parameters sample tested.

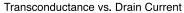
## **Switching Waveforms and Test Circuit**

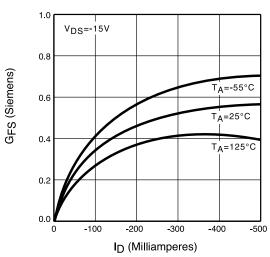


<sup>#</sup> Mounted on FR5 board, 25mm x 25mm x 1.57mm.

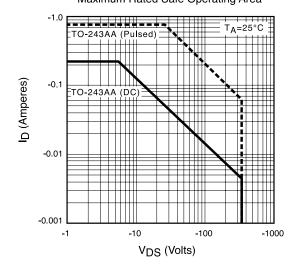
## **Typical Performance Curves**



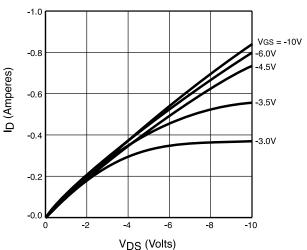




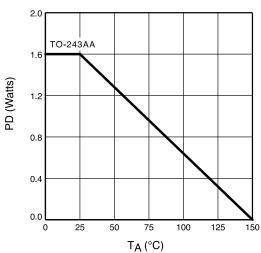
Maximum Rated Safe Operating Area



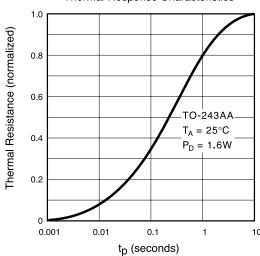
### Saturation Characteristics



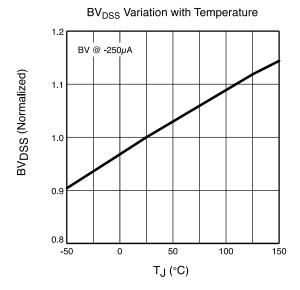
#### Power Dissipation vs. Ambient Temperature

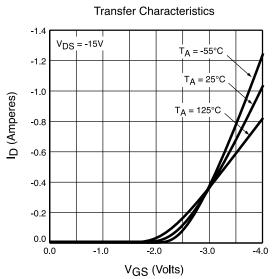


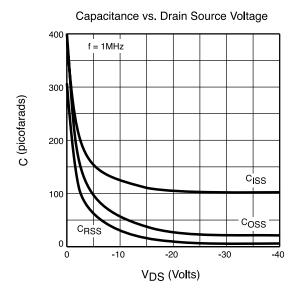
#### Thermal Response Characteristics

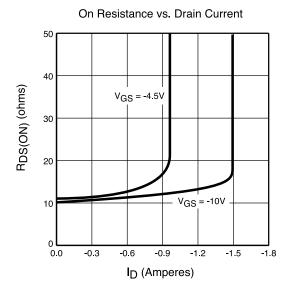


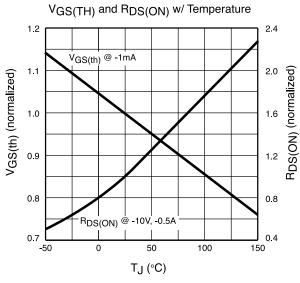
## **Typical Performance Curves** (cont.)

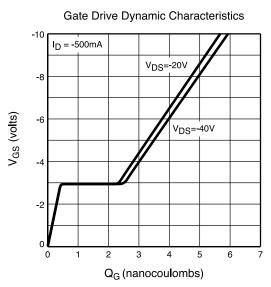




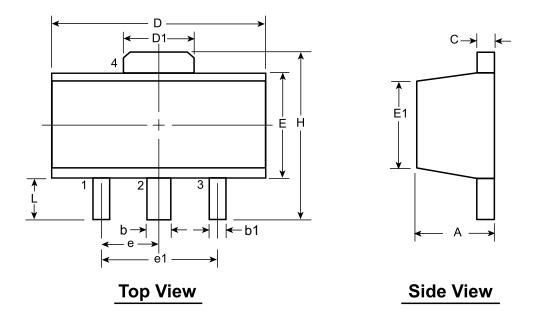








# 3-Lead TO-243AA (SOT-89) Package Outline (N8)



Symbo	ol	Α	b	b1	С	D	D1	E	E1	е	e1	Н	L
Dimensions (mm)	MIN	1.40	0.44	0.36	0.35	4.40	1.62	2.29	2.13	1.50 3.00 BSC BSC		3.94	0.89
	NOM	-	-	-	-	-	-	-	-		-	-	
	MAX	1.60	0.56	0.48	0.44	4.60	1.83	2.60	2.29		200	4.25	1.20

JEDEC Registration TO-243, Variation AA, Issue C, July 1986.

Drawings not to scale.

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